## **NSD070AL**

# **Switching Diode**

#### **Features**

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	70	V
Forward Current (DC)	I <sub>F</sub>	200	mA
Non-Repetitive Peak Forward Current t = 1.0 s	I <sub>FSM</sub>	500	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

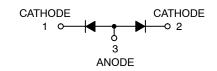


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CASE 318 SOT-23



## **MARKING DIAGRAM**



JY = Specific Device Code

M = Date Code\*

■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NSD070ALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NSVD070ALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### NSD070AL

## THERMAL CHARACTERISTICS

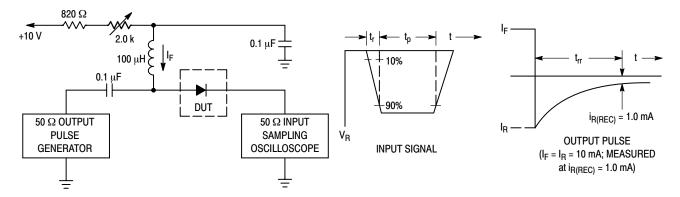
Characteristic	Symbol	Min	Тур	Max	Unit
Thermal Resistance Junction-to-Ambient (Note 1) Total Device Dissipation @ T <sub>A</sub> = 25°C	R <sub>θJA</sub> P <sub>D</sub>	1 1	-	556 225	°C/W mW
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-	_	-65 to +150	°C

<sup>1.</sup> FR-4 =  $1.0 \times 0.75 \times 0.062$  in.

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	<u>.</u>				
Reverse Breakdown Voltage (V <sub>R</sub> = 70 Vdc)	V <sub>(BR)</sub>	70	-	-	V
Reverse Voltage Leakage Current (V <sub>R</sub> = 70 Vdc) (V <sub>R</sub> = 70 Vdc, T <sub>J</sub> = 150°C)	IR	- -	- -	5.0 80	nA
Diode Capacitance (V <sub>R</sub> = 0 V, f = 1.0 MHz)	C <sub>D</sub>	_	1.0	2.0	pF
Forward Voltage (I <sub>F</sub> = 1.0 mA) (I <sub>F</sub> = 10 mA) (I <sub>F</sub> = 50 mA) (I <sub>F</sub> = 150 mA)	V <sub>F</sub>	- - - -	- - - -	900 1000 1100 1250	mV
Reverse Recovery Time (I <sub>F</sub> = I <sub>R</sub> = 10 mA) (Figure 1)	t <sub>rr</sub>	-	_	3.0	μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



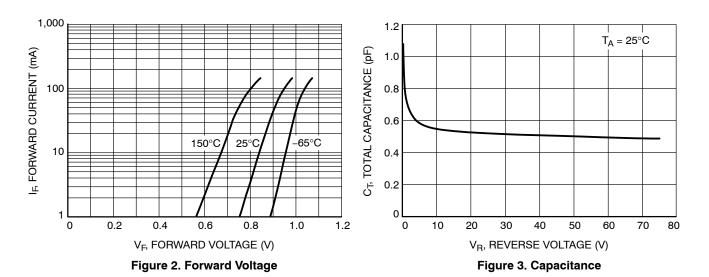
Notes: 1. A 2.0  $k\Omega$  variable resistor adjusted for a Forward Current (I\_F) of 10 mA.

- 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10 mA.
- 3.  $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

## NSD070AL

## **TYPICAL CHARACTERISTICS**





SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

**DATE 30 JAN 2018** 

# SCALE 4:1 D - 3X b

**TOP VIEW** 







### **RECOMMENDED SOLDERING FOOTPRINT**



DIMENSIONS: MILLIMETERS

#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

	PROT	RUSIONS, OR GATE BURRS.	
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	MILLIMETERS			TERS INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

## **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
<ol><li>ANODE</li></ol>	<ol><li>SOURCE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. DRAIN	2. GATE
<ol><li>CATHODE</li></ol>	3. GATE	<ol><li>CATHODE-ANODE</li></ol>	<ol><li>ANODE</li></ol>	3. GATE	<ol><li>ANODE</li></ol>

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. ANODE	<ol><li>CATHODE</li></ol>	2. ANODE	<ol><li>ANODE</li></ol>
<ol><li>ANODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>CATHODE-ANOD</li></ol>	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
<ol><li>SOURCE</li></ol>	<ol><li>OUTPUT</li></ol>	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	<ol><li>NO CONNECTION</li></ol>

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
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IDWD50E120D7XKSA1 IDWD60E120D7XKSA1 IDWD75E120D7XKSA1 BAS21TWQ-7 BAV21WQ-7-F MMBD4448HADWQ-7-F
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